

MSKSEMI 美森科

SEMICONDUCTOR



ESD



TVS



TSS



MOV



GDT



PLED

MMBT3904

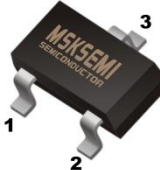

Product specification

TRANSISTOR (NPN)

FEATURES

- Complementary to MMBT3906

Reference News

PACKAGE OUTLINE	MARKING
 <div> 1. BASE 2. EMITTER 3. COLLECTOR </div>	
SOT-23	

MAXIMUM RATINGS (Ta=25°C unless otherwise noted)

Symbol	Parameter	Value	Unit
V_{CBO}	Collector-Base Voltage	60	V
V_{CEO}	Collector-Emitter Voltage	40	V
V_{EBO}	Emitter-Base Voltage	6	V
I_C	Collector Current	200	mA
P_C	Collector Power Dissipation	200	mW
R_{JA}	Thermal Resistance From Junction To Ambient	625	°C/W
T_J, T_{stg}	Operation Junction and Storage Temperature Range	-55~+150	°C

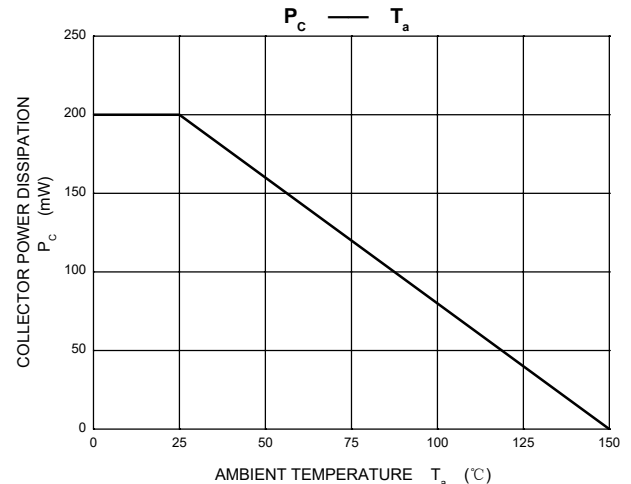
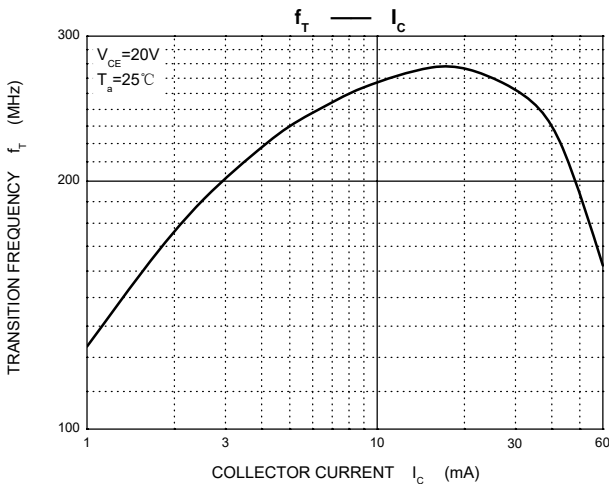
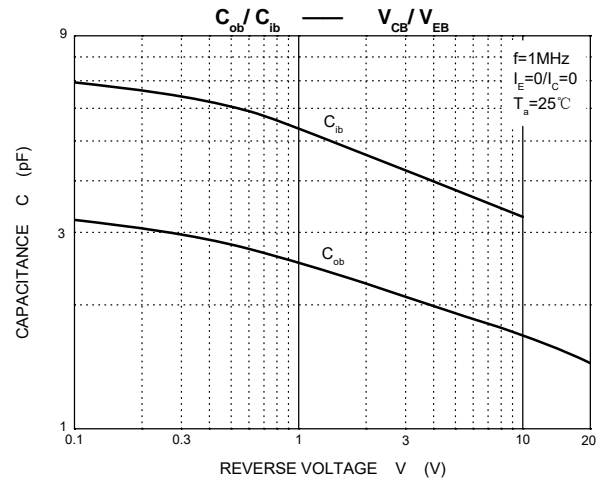
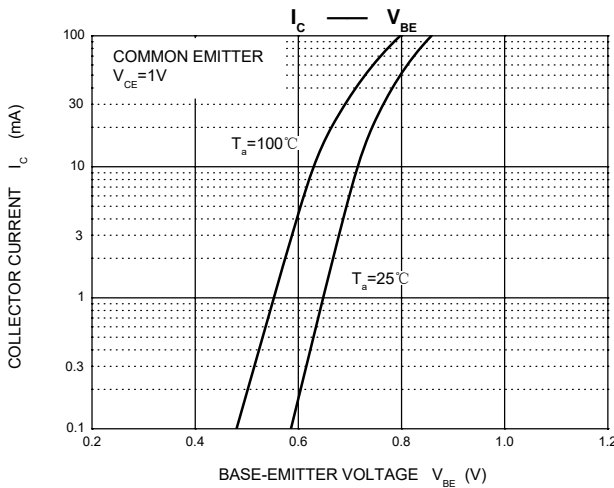
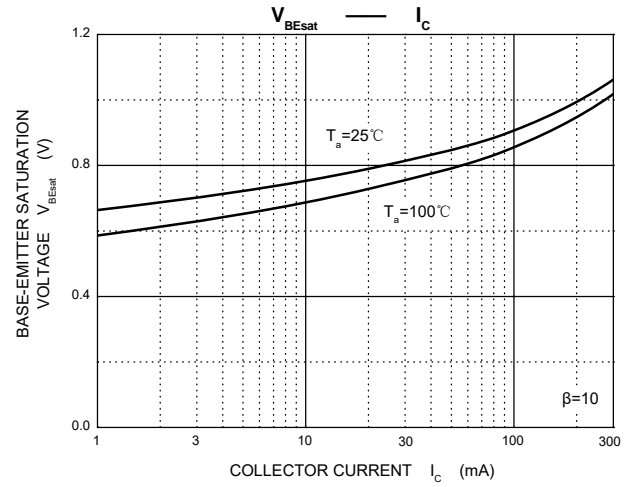
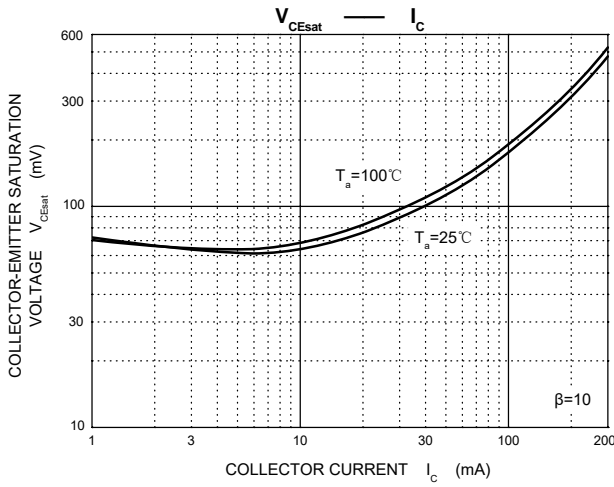
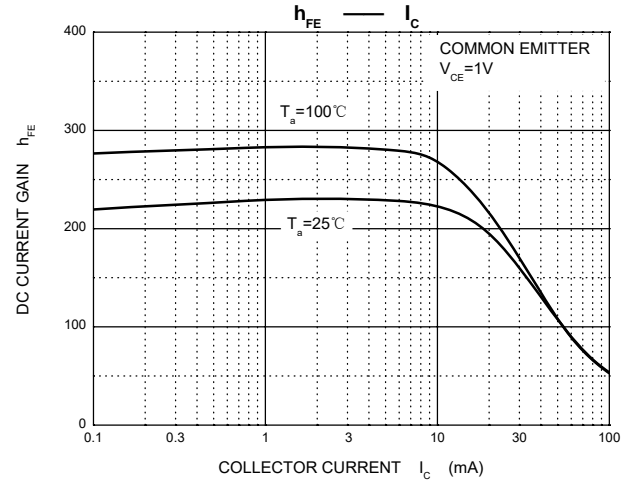
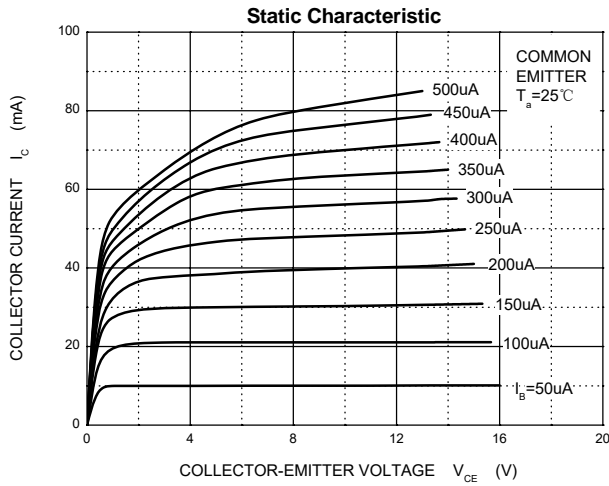
ELECTRICAL CHARACTERISTICS (Ta=25°C unless otherwise specified)

Parameter	Symbol	Test conditions	Min	Typ	Max	Unit
Collector-base breakdown voltage	$V_{(BR)CBO}$	$I_C=10\mu A, I_E=0$	60			V
Collector-emitter breakdown voltage	$V_{(BR)CEO}$	$I_C=1mA, I_B=0$	40			V
Emitter-base breakdown voltage	$V_{(BR)EBO}$	$I_E=10\mu A, I_C=0$	6			V
Collector cut-off current	I_{CEX}	$V_{CE}=30V, V_{EB(off)}=3V$			50	nA
Collector cut-off current	I_{CBO}	$V_{CB}=60V, I_E=0$			100	nA
Emitter cut-off current	I_{EBO}	$V_{EB}=5V, I_C=0$			100	nA
DC current gain	$h_{FE(1)}$	$V_{CE}=1V, I_C=10mA$	100		300	
	$h_{FE(2)}$	$V_{CE}=1V, I_C=50mA$	60			
	$h_{FE(3)}$	$V_{CE}=1V, I_C=100mA$	30			
Collector-emitter saturation voltage	$V_{CE(sat)}$	$I_C=50mA, I_B=5mA$			0.3	V
Base-emitter saturation voltage	$V_{BE(sat)}$	$I_C=50mA, I_B=5mA$			0.95	V
Transition frequency	f_T	$V_{CE}=20V, I_C=10mA, f=100MHz$	300			MHz
Delay time	t_d	$V_{CC}=3V, V_{BE(off)}=-0.5V, I_C=10mA, I_{B1}=1mA$			35	ns
Rise time	t_r	$V_{CC}=3V, V_{BE(off)}=-0.5V, I_C=10mA, I_{B1}=1mA$			35	ns
Storage time	t_s	$V_{CC}=3V, I_C=10mA, I_{B1}=I_{B2}=1mA$			200	ns
Fall time	t_f	$V_{CC}=3V, I_C=10mA, I_{B1}=I_{B2}=1mA$			50	ns

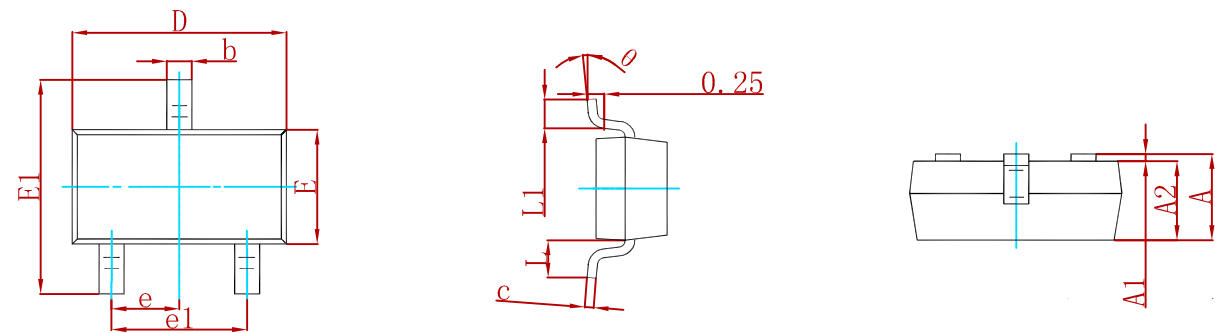
CLASSIFICATION OF $h_{FE(1)}$

HFE	100-300	
RANK	L	H
RANGE	100 - 200	200 - 300

Typical Characteristics

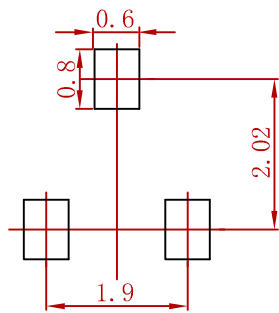


PACKAGE MECHANICAL DATA



Symbol	Dimensions In Millimeters		Dimensions In Inches	
	Min	Max	Min	Max
A	0.900	1.150	0.035	0.045
A1	0.000	0.100	0.000	0.004
A2	0.900	1.050	0.035	0.041
b	0.300	0.500	0.012	0.020
c	0.080	0.150	0.003	0.006
D	2.800	3.000	0.110	0.118
E	1.200	1.400	0.047	0.055
E1	2.250	2.550	0.089	0.100
e	0.950 TYP		0.037 TYP	
e1	1.800	2.000	0.071	0.079
L	0.550 REF		0.022 REF	
L1	0.300	0.500	0.012	0.020
θ	0°	8°	0°	8°

Suggested Pad Layout



Note:
1.Controlling dimension:in millimeters.
2.General tolerance:± 0.05mm.
3.The pad layout is for reference purposes only.

REEL SPECIFICATION

P/N	PKG	QTY
MMBT3904	SOT-23	3000

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